TECHNICAL DATA DATASHEET 1138, REV. D

HV MOSFET Power Module Data Sheet

DESCRIPTION: 3000 VOLT, 1.0 AMP, INDUSTRIAL MOSFET POWER MODULE

ELECTRICAL CHARACTERISTICS

(AT Tj=25°C UNLESS OTHERWISE SPECIFIED)

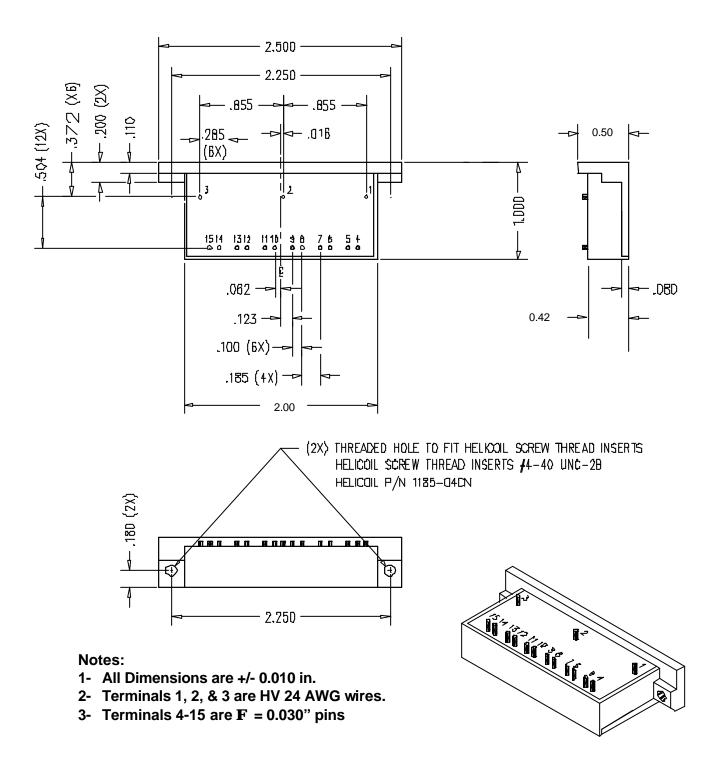
PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
POWER MOSFETS Q1,,6						
Drain-to-Source Breakdown Voltage for	V _{(BR)DSS}	$V_{GS}=0V,I_{D}=0.5 \text{ mA},$				
each one of Q1,2,,6	, , , ,	T _j = 25 °C	1000	-	-	V
Drain-to-Source Leakage Current	I _{DSS}	V _{GS} =0V,	-	-		
		$V_{DS}=1000V$, $T_{j}=25$ °C			0.250	mA
		$V_{DS}=1000V$, $T_{j}=125$ °C			2	
Continuous Drain Current	l _D	V _{GS} =10V	-	-	1	Α
Maximum Pulsed Drain Current (1)	I _{DM}	$T_C = 25$ °C	-	-	4	Α
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$	2.0	-	4.0	V
		$I_D = 0.50 \text{mA}$				
Static Drain-to-Source On Resistance	R _{DS}	$V_{GS} = 10 \text{ V}, I_D = 0.80 \text{ A}$	-		11.0	Ω
Input Capacitance	C _{iss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$	-	500	-	pF
Output Capacitance	Coss	f = 1 MHz		52		
Reverse Transfer Cap.	C _{rss}			17		
Total Gate Charge	Q_G	$V_{GS} = 10 \text{ V}, I_{D} = 1 \text{ A},$			38	nC
		$V_{DD} = 400 \text{ V}$				
Turn-on Delay	$t_{d(on)}$	$V_{DD} = 500 \text{ V}, V_{GS} = 10 \text{ V},$	-	10	-	ns
Rise Time	t _r	I _D = 1.0 A		17		
Turn-off Delay	$t_{d(off)}$			58		
Fall Time	t _f			31		
Junction to Base Thermal Resistance	R _{thjc}				3.7	°C/W
Nominal Gate-to-source Zener Breakdown	Vz		±17.5	±18.0	±19.0	V
Voltage, $I_Z = 1mA$						
Operating and Storage Junction	T _j		-40		100	°C
Temperature						
Operating Case Temperature	T _j		-40		100	°C
Pin-To-Base plate Voltage Isolation	V _{iso}	1 minute, at sea level			10,000	V
DIODE CHARACTERISTICSD1	D2, D3					
Forward Voltage	V _F	I _F = 1A	-	-	1.1	V
Reverse Recovery Time	t _{rr}	$T_j = 25$ °C, $I_F = 1$ A,	-	-	150	ns
		$di/dt = 50 \text{ A}/ \mu \text{s}, V_{rr} = 400 \text{V}$				
GATE DRIVE MOSFETs Q7,,	18 ⁽¹⁾ CHAF	RACTERISTICS				
Turn-On Time	t _{on}		-	-	20	ns
Turn-Off Time	t _{off}		-	-	20	ns

Notes,

¹⁻ Type 2N7002 or similar.

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MECHANICAL DRAWING - In inches





TECHNICAL DATA

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